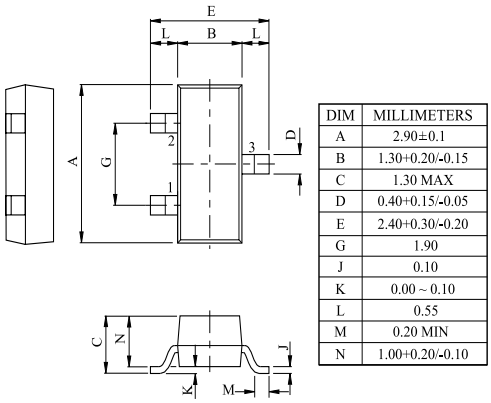
KTC9015SC

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES

- Excellent h_{FE} Linearity
  : $h_{FE}(I_C$=-0.1mA)/$h_{FE}(I_C$=-2mA)=0.95(Typ.).
- Complementary to KTC9014SC.



DIM	MILLIMETERS
A	2.90±0.1
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.40+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
J	0.10
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10

1. EMITTER
2. BASE
3. COLLECTOR

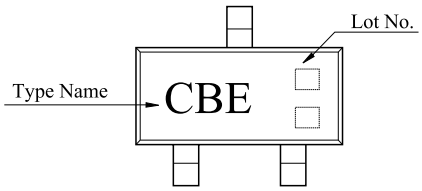
SOT-23(1)

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-70	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C *	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

* P_C : Package Mounted On 99.5% Alumina (10×8×0.6㎜)

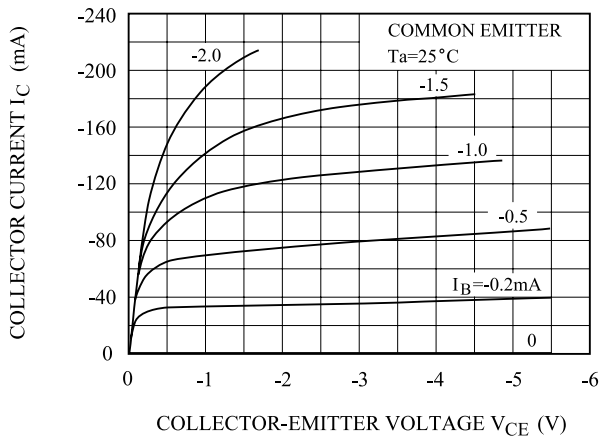
Marking



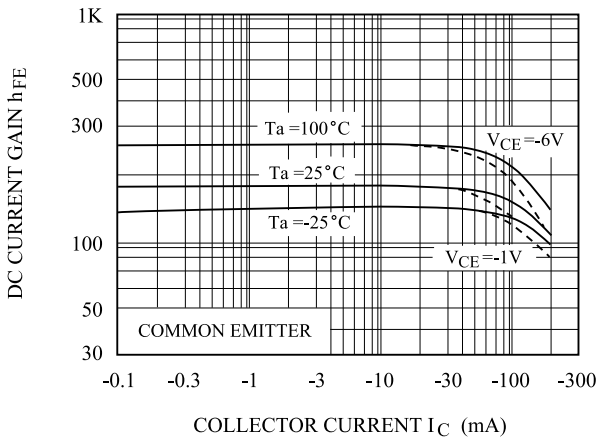
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-0.05mA, I_E=0	-70	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-0.05mA, I_C=0	-8	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB}=-50V, I_E=0	-	-	-0.1	uA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-0.1	uA
DC Current Gain	h_{FE}	V_{CE}=-5V, I_C=1mA	200	-	300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-5mA	-	-	-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-5mA	-	-	-1	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-10mA, f=30MHz	150	-	-	MHz

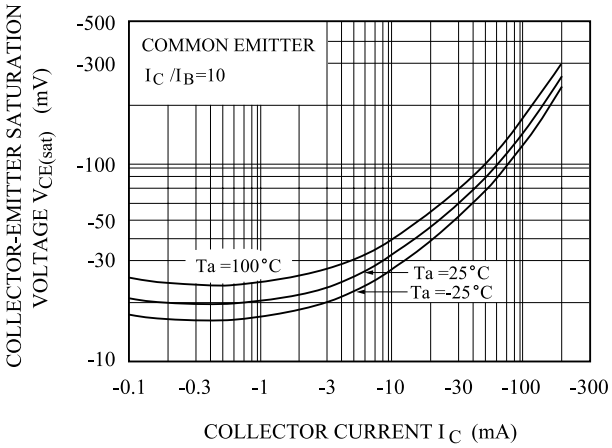
I_C - V_{CE}



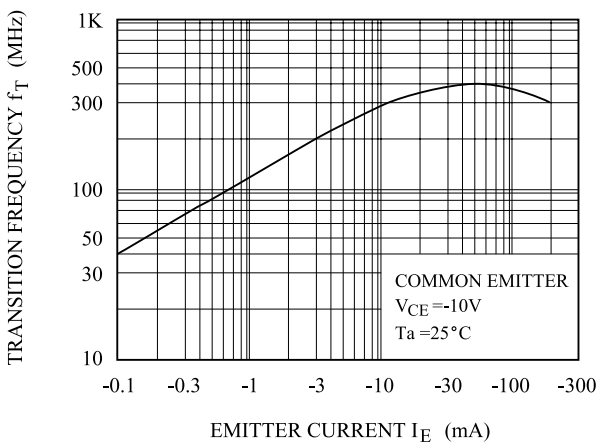
h_{FE} - I_C



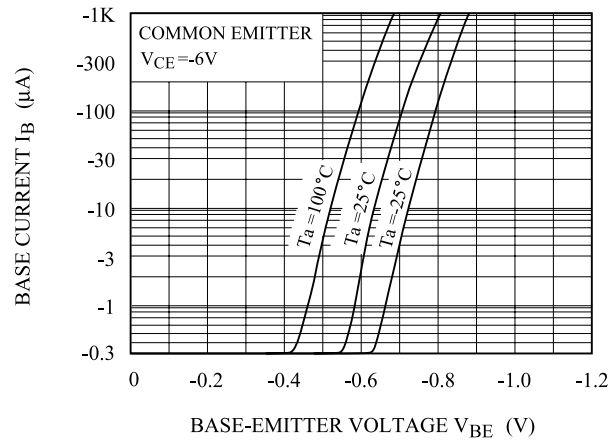
$V_{CE(sat)}$ - I_C



f_T - I_E



I_B - V_{BE}



Pc - Ta